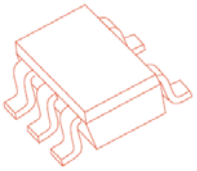
General purpose transistors (dual transistors)

SOT-353

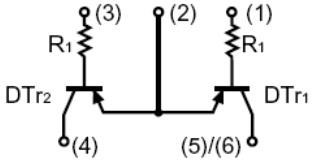


FEATURES

- Two DTA143T chips in a package
- Mounting cost and area be cut in half

Marking: A3

Equivalent circuit



Absolute maximum ratings (Ta=25℃)

Symbol	Parameter	Limits	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-100	mA
P_C	Collector Dissipation	150	mW
T_j	Junction temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			- 0.5	μA
DC current gain	h_{FE}	V_{CE}=-5V,I_C=-1mA	100		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-5mA,I_B=-0.25mA			-0.3	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-5mA, f=100MHz		250		MHz
Input resistor	R_1		3.29	4.7	6.11	KΩ